

5DS10B

Switching Diode

PHENITEC
SEMICONDUCTOR

Features

- High-speed

Item	Characteristics
Wafer size	5inch
Chip size	235*235um
Chip Thickness	95±20um
Bump Height	30±15um
Top Metalization	Ti-Ag+Ag Bump
Back Metalization	Ti-Ni-Ag
Dicing	Half Cut

Maximum Ratings @25degC

Item	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	VRSM	100	V
Repetitive Peak Reverse Voltage	VRRM	75	V
Repetitive Peak Forward Current	IFRM	500	mA
Continuous Forward Current	IO	150	mA
Non-Repetitive Peak Forward Current @t=1us	IFSM	2	A
Power Dissipation	PD	500	mW
Junction Temperature	Tj	175	degC
Storage Temperature	Tstg	-65to+175	degC

Electrical Characteristics @25degC

Item	Symbol	Min	Max	Unit	Test Condition
Forward Voltage	VF		1	V	IF=10mA
Reverse Current	IR		25	nA	VR=20V
Reverse Current	IR		5	uA	VR=75V
Junction Capacitance	CT		4	pF	VR=0V, f=1MHz
Reverse Recovery Time	trr		4	nsec	IF=10mA, VR=6V, RL=100Ω, irr=1mA

Probing Spec @25degC

Symbol	Min	Max	Unit	Test Condition
VF1		850	mV	IF=10mA
VF2		1	V	IF=100mA
VF3		1.3	V	IF=200mA
IR1		25	nA	VR=30V
IR2		100	nA	VR=75V
IR2		200	nA	VR=100V
BV	135		V	IR=50uA
CT		4	pF	VR=0V, f=1MHz
trr		4	nsec	IF=10mA, VR=6V, RL=100Ω, irr=1mA

Note

Equivalent type : 1N4148

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